

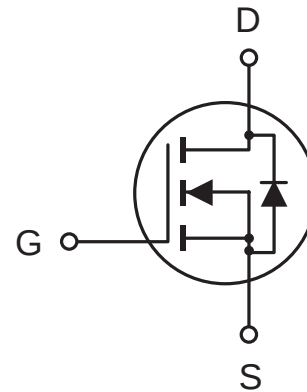
CED01N6/CEU01N6

PRELIMINARY

N-Channel Logic Level Enhancement Mode Field Effect Transistor

FEATURES

- 600V , 1.3A , $R_{DS(ON)}=7.5\Omega$ @ $V_{GS}=10V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- TO-251 & TO-252 package.



ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage	V _{GS}	± 30	V
Drain Current-Continuous (T _c =25°C)	I _D	1.3	A
-Continuous (T _c =100°C)		0.85	A
Drain Current-Pulsed	I _{DM}	3.9	A
Drain-Source Diode Forward Current	I _S	1.3	A
Maximum Power Dissipation @T _c =25°C Derate above 25°C	P _D	35	W
		0.29	W/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R _{θJC}	3.5	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	50	°C/W

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ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE AVALANCHE RATING^a						
Single Pulse Drain-Source Avalanche Energy	E _{AS}	V _{DD} =50V, L=95mH R _G =25Ω		90		mJ
Maximum Drain-Source Avalanche Current	I _{AS}			1.3		A
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	600			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			25	μA
Gate-Body Leakage	I _{GSS}	V _{GS} = ± 30V, V _{DS} = 0V			±100	nA
ON CHARACTERISTICS^a						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2		4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D = 0.65A		5.5	7.5	Ω
Forward Transconductance	g _{FS}	V _{DS} = 50V, I _D = 0.65A		0.9		S
SWITCHING CHARACTERISTICS^b						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 300V, I _D = 1A, V _{GS} = 10V R _{GEN} =25Ω		6	18	ns
Rise Time	t _r			25	50	ns
Turn-Off Delay Time	t _{D(OFF)}			10	30	ns
Fall Time	t _f			20	50	ns
Total Gate Charge	Q _g	V _{DS} =480V, I _D = 1A, V _{GS} =10V		8	12	nC
Gate-Source Charge	Q _{gs}			1.3		nC
Gate-Drain Charge	Q _{gd}			3		nC

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ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS ^b						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} = 0V f =1.0MHz		200		pF
Output Capacitance	C _{OSS}			30		pF
Reverse Transfer Capacitance	C _{RSS}			10		pF
DRAIN-SOURCE DIODE CHARACTERISTICS ^a						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S =1.3A			1.5	V

Notes

a. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

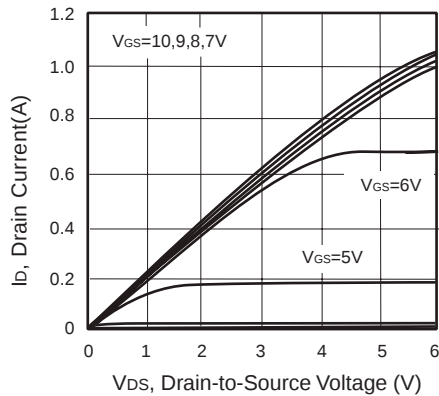


Figure 1. Output Characteristics

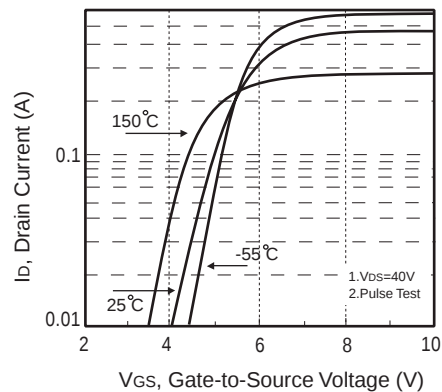


Figure 2. Transfer Characteristics

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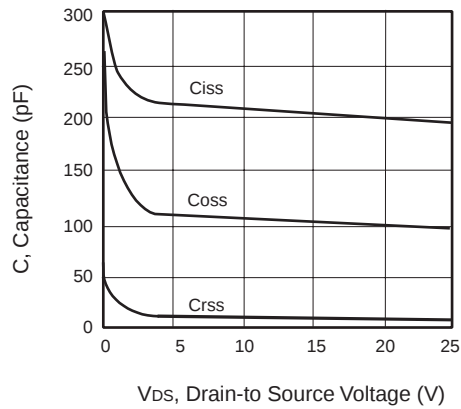


Figure 3. Capacitance

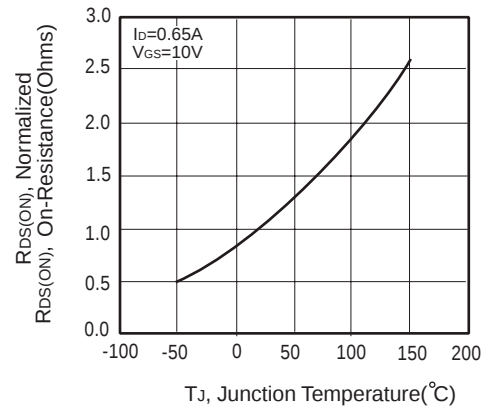


Figure 4. On-Resistance Variation with Temperature

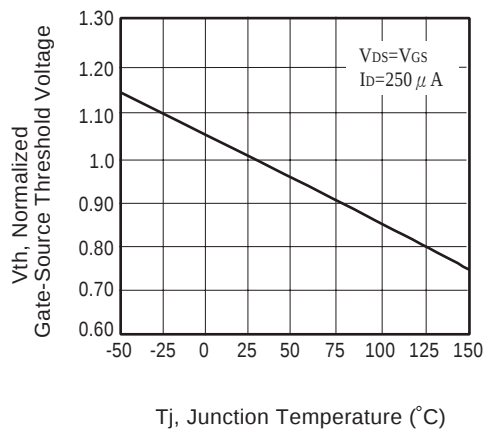


Figure 5. Gate Threshold Variation with Temperature

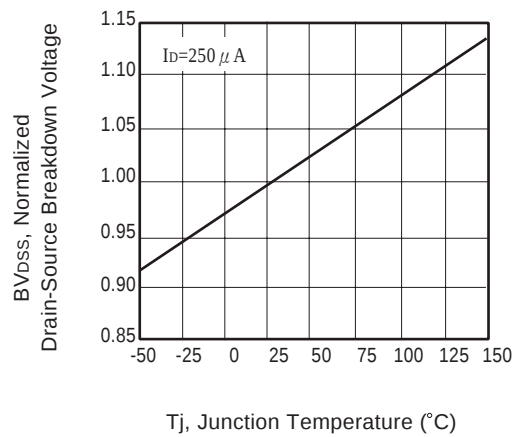


Figure 6. Breakdown Voltage Variation with Temperature

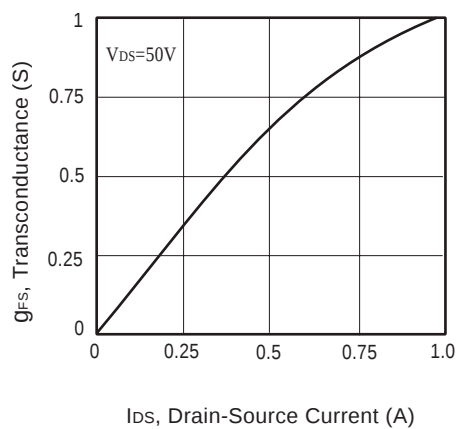


Figure 7. Transconductance Variation with Drain Current

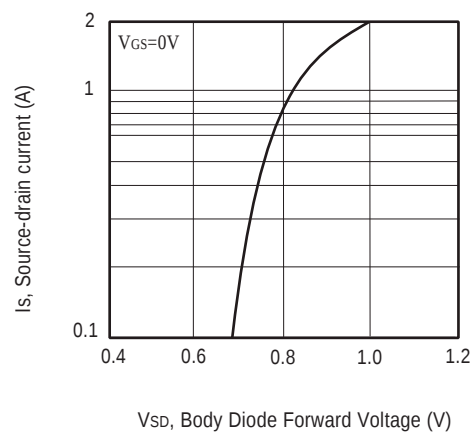


Figure 8. Body Diode Forward Voltage Variation with Source Current

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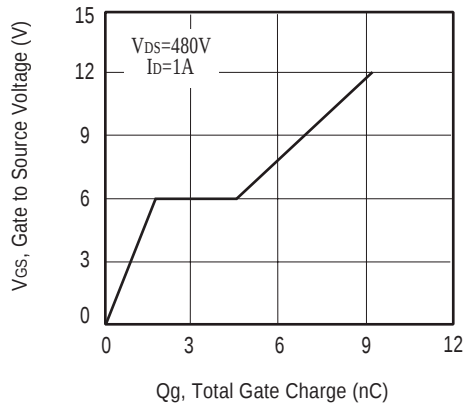


Figure 9. Gate Charge

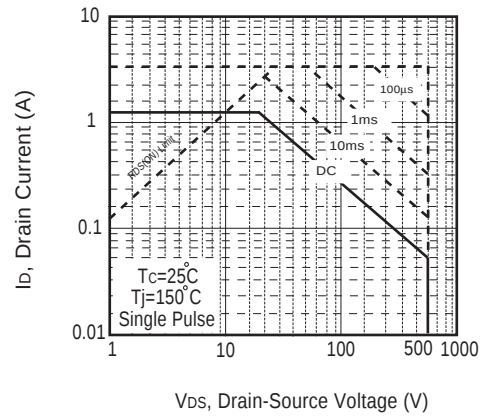


Figure 10. Maximum Safe Operating Area

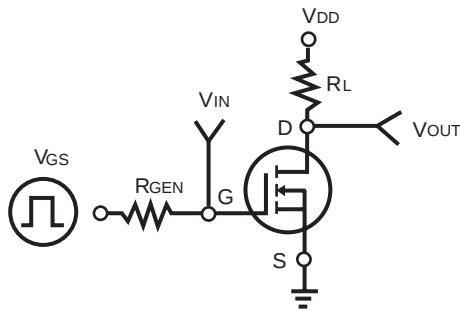


Figure 11. Switching Test Circuit

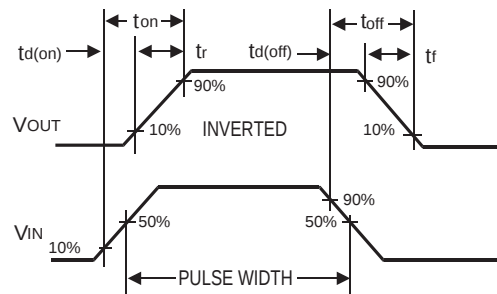


Figure 12. Switching Waveforms

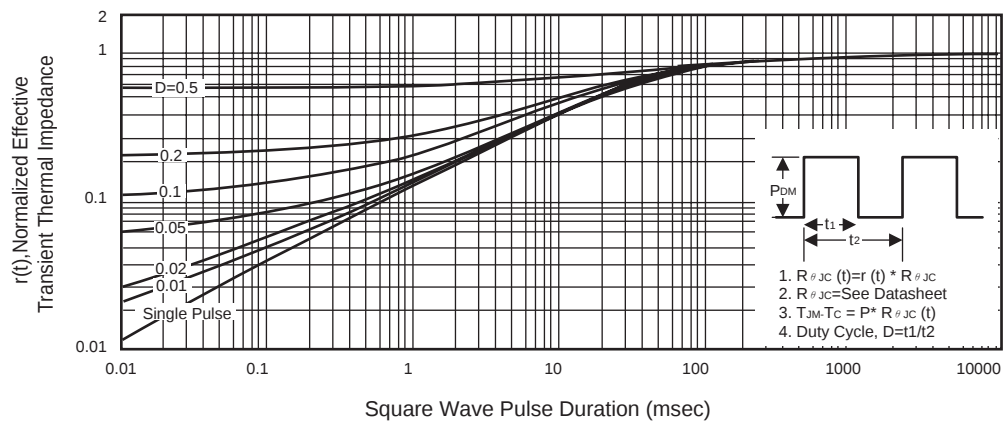


Figure 13. Normalized Thermal Transient Impedance Curve